



PDTC114TMB

NPN resistor-equipped transistor; R1 = 10 k Ω , R2 = open

Rev. 1 — 21 June 2012

Product data sheet

1. Product profile

1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA114TMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

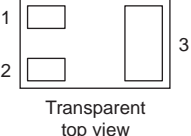
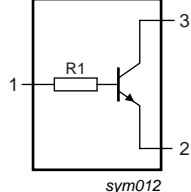
Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|---------------------------|--------------------------|-----|-----|-----|------------|
| V _{CEO} | collector-emitter voltage | open base | - | - | 50 | V |
| I _O | output current | | - | - | 100 | mA |
| R1 | bias resistor 1 (input) | T _{amb} = 25 °C | 7 | 10 | 13 | k Ω |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|--------------------|--------------------------------------------------------------------------------------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------|
| 1 | I | input (base) |  <p>Transparent top view</p> <p>DFN1006B-3 (SOT883B)</p> |  <p><i>sym012</i></p> |
| 2 | G | GND (emitter) | | |
| 3 | O | output (collector) | | |

3. Ordering information

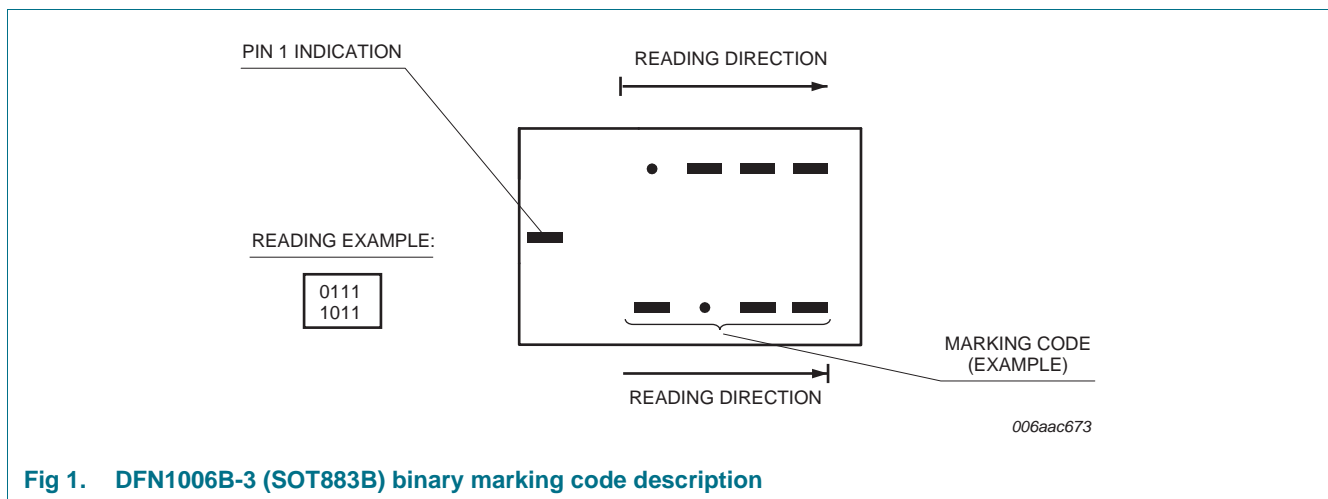
Table 3. Ordering information

| Type number | Package | | |
|-------------|------------|--------------------------------------------------------------------------------|---------|
| | Name | Description | Version |
| PDTC114TMB | DFN1006B-3 | Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm | SOT883B |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PDTC114TMB | 0010 1111 |



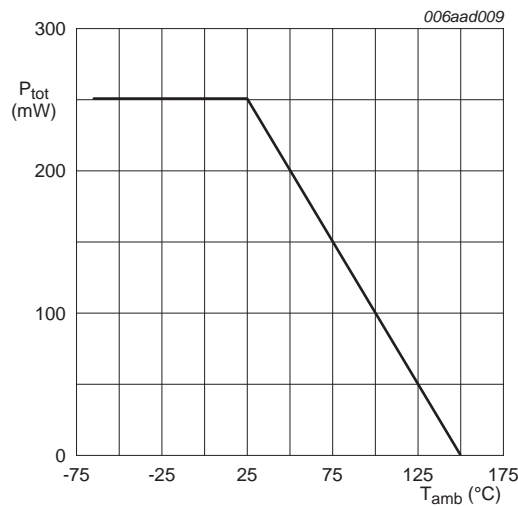
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|-------------------------------|-----|-----|------|
| V _{CBO} | collector-base voltage | open emitter | - | 50 | V |
| V _{CEO} | collector-emitter voltage | open base | - | 50 | V |
| V _{EBO} | emitter-base voltage | open collector | - | 5 | V |
| I _O | output current | | - | 100 | mA |
| I _{CM} | peak collector current | pulsed; t _p ≤ 1 ms | - | 100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | 250 | mW |
| T _j | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | 150 | °C |
| T _{stg} | storage temperature | | -65 | 150 | °C |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

Fig 2. Power derating curve for DFN1006B-3 (SOT883B)

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|---------------------------------------------|---------------------------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air [1] | - | - | 500 | K/W |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

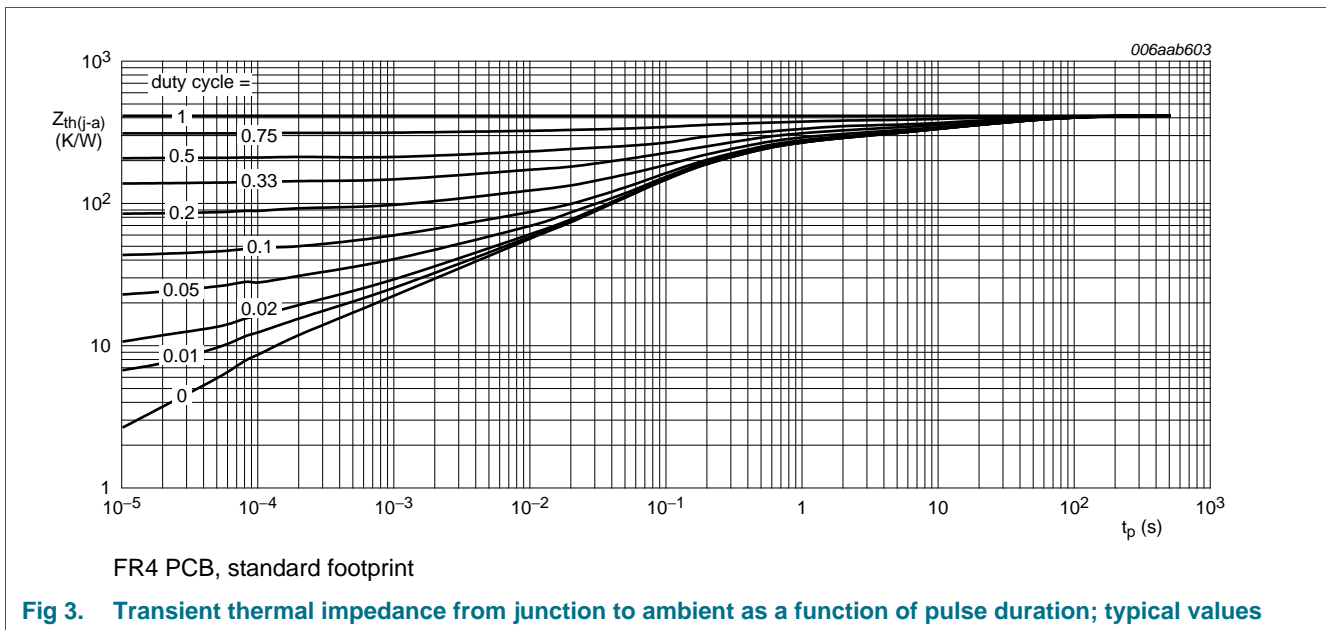


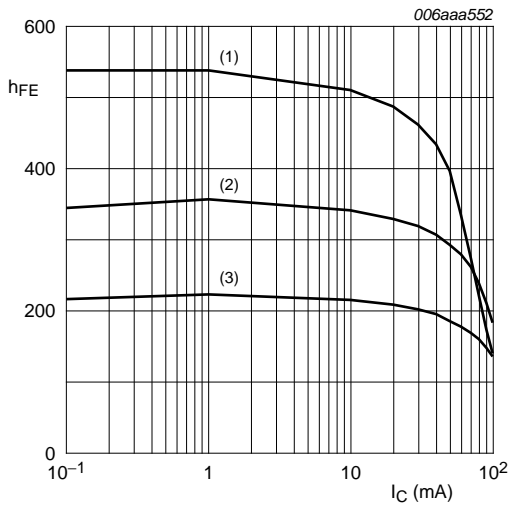
Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

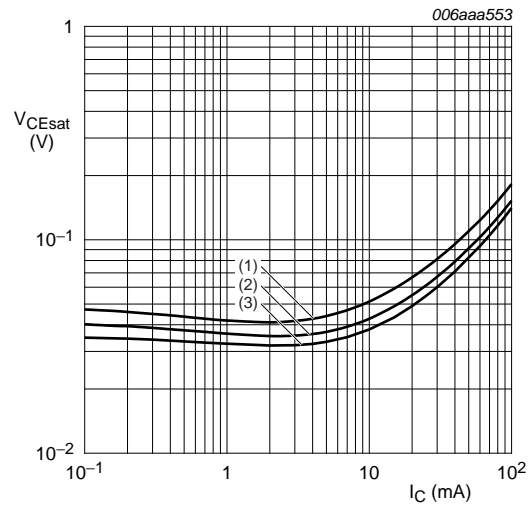
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------|--------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|-----|-----|--------|---------------|
| I_{CBO} | collector-base cut-off current | $V_{CB} = 50\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ °C}$ | - | - | 100 | nA |
| I_{CEO} | collector-emitter cut-off current | $V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_{amb} = 25\text{ °C}$ $V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ °C}$ | - | - | 1 5 | μA |
| I_{EBO} | emitter-base cut-off current | $V_{EB} = 5\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ °C}$ | - | - | 100 | nA |
| h_{FE} | DC current gain | $V_{CE} = 5\text{ V}; I_C = 1\text{ mA}; T_{amb} = 25\text{ °C}$ | 200 | - | - | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 10\text{ mA}; I_B = 0.5\text{ mA}; T_{amb} = 25\text{ °C}$ | - | - | 150 | mV |
| R1 | bias resistor 1 (input) | $T_{amb} = 25\text{ °C}$ | 7 | 10 | 13 | kΩ |
| C_C | collector capacitance | $V_{CB} = 10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A}; f = 1\text{ MHz}; T_{amb} = 25\text{ °C}$ | - | - | 2.5 | pF |
| f_T | transition frequency | $V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}; T_{amb} = 25\text{ °C}$ [1] | - | 230 | - | MHz |

[1] Characteristics of built-in transistor.



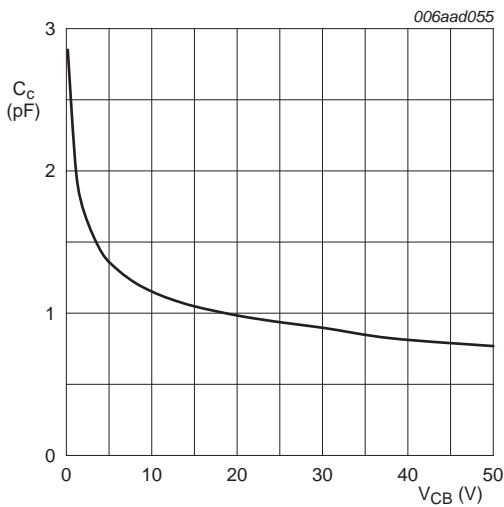
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig 4. DC current gain as a function of collector current; typical values



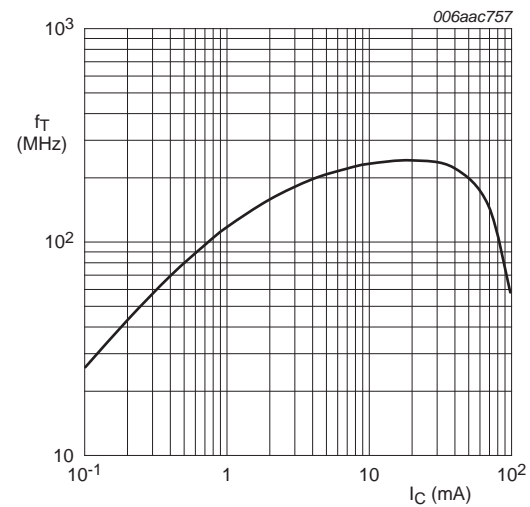
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -40\text{ }^\circ\text{C}$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



$f = 1\text{ MHz}; T_{amb} = 25\text{ }^\circ\text{C}$

Fig 6. Collector capacitance as a function of collector-base voltage; typical values of built-in transistor



$V_{CE} = 5\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$

Fig 7. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline

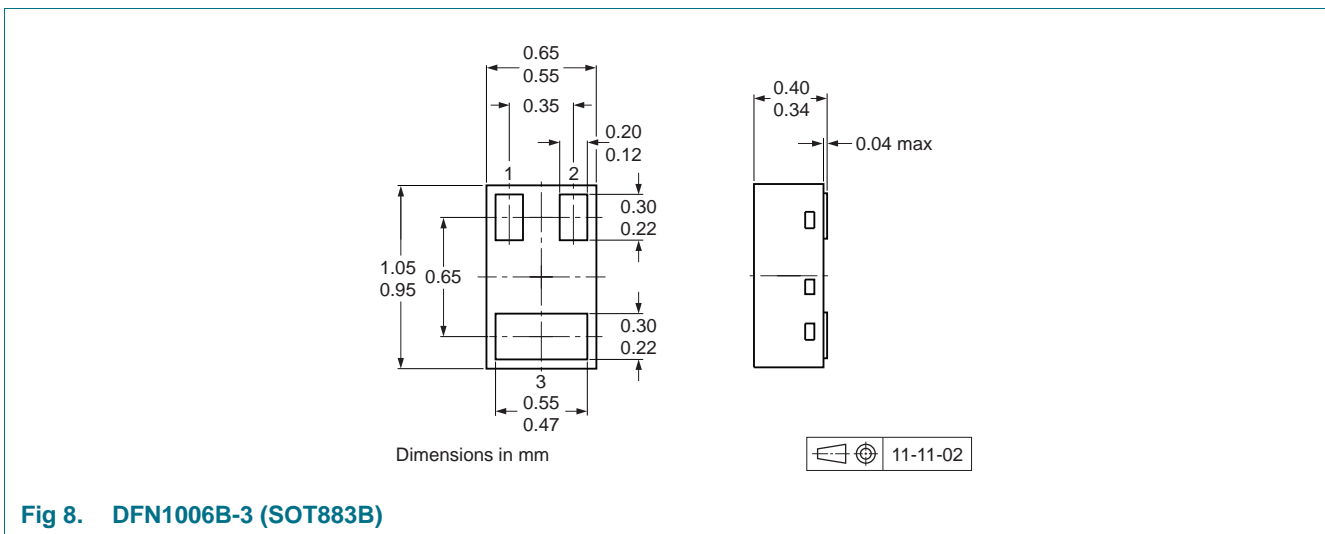
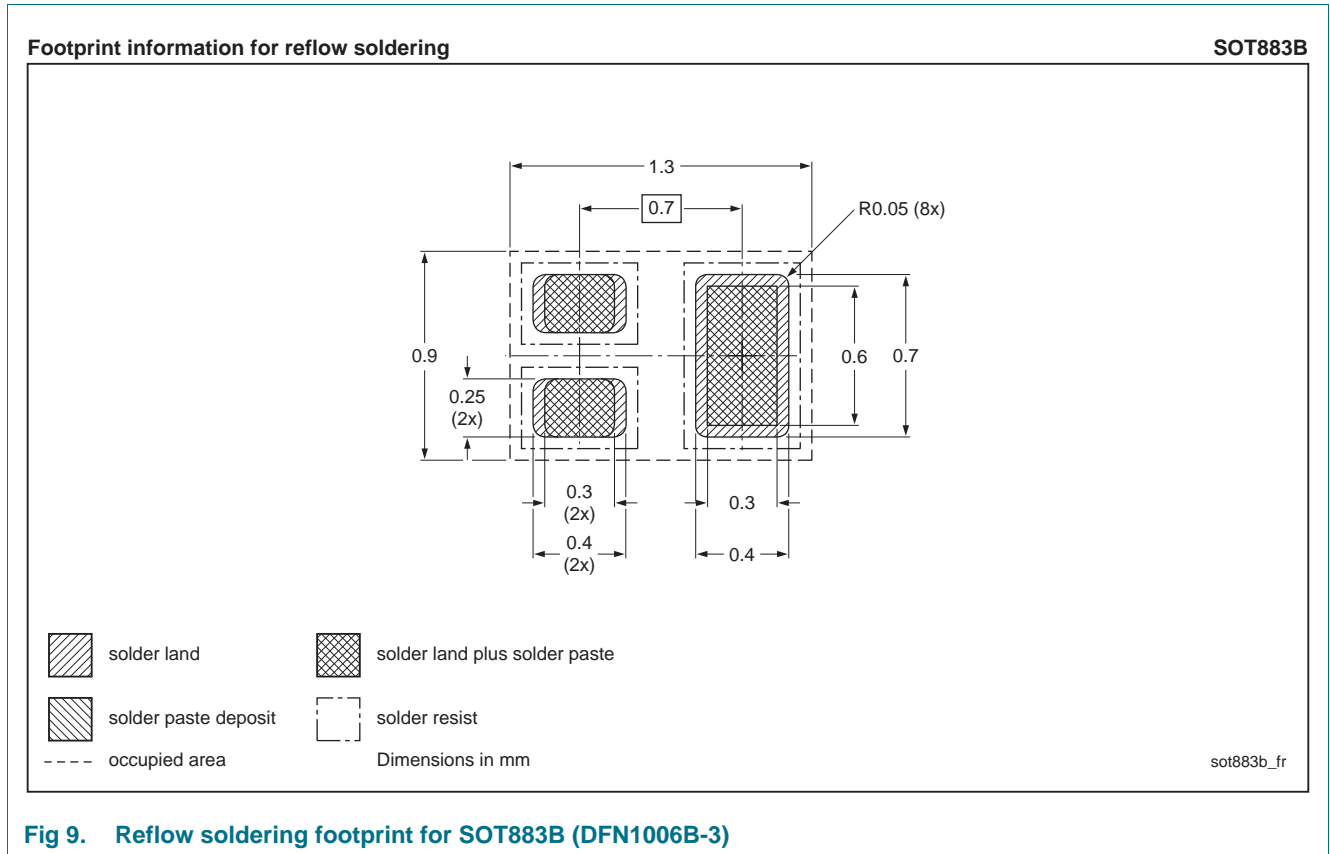


Fig 8. DFN1006B-3 (SOT883B)

10. Soldering



11. Revision history

Table 8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|--------------------|---------------|------------|
| PDTC114TMB v.1 | 20120621 | Product data sheet | - | - |

12. Legal information

12.1 Data sheet status

| Document status ^{[1] [2]} | Product status ^[3] | Definition |
|------------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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